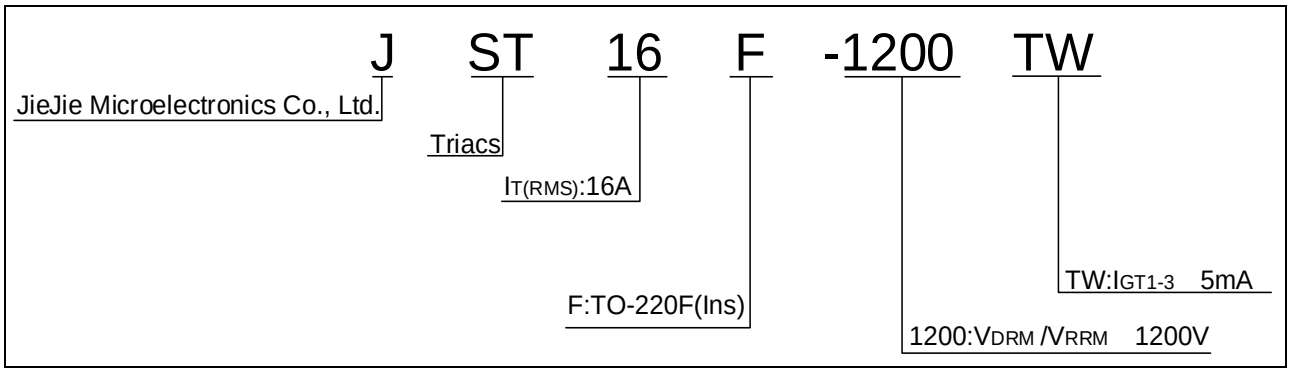
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3	kV

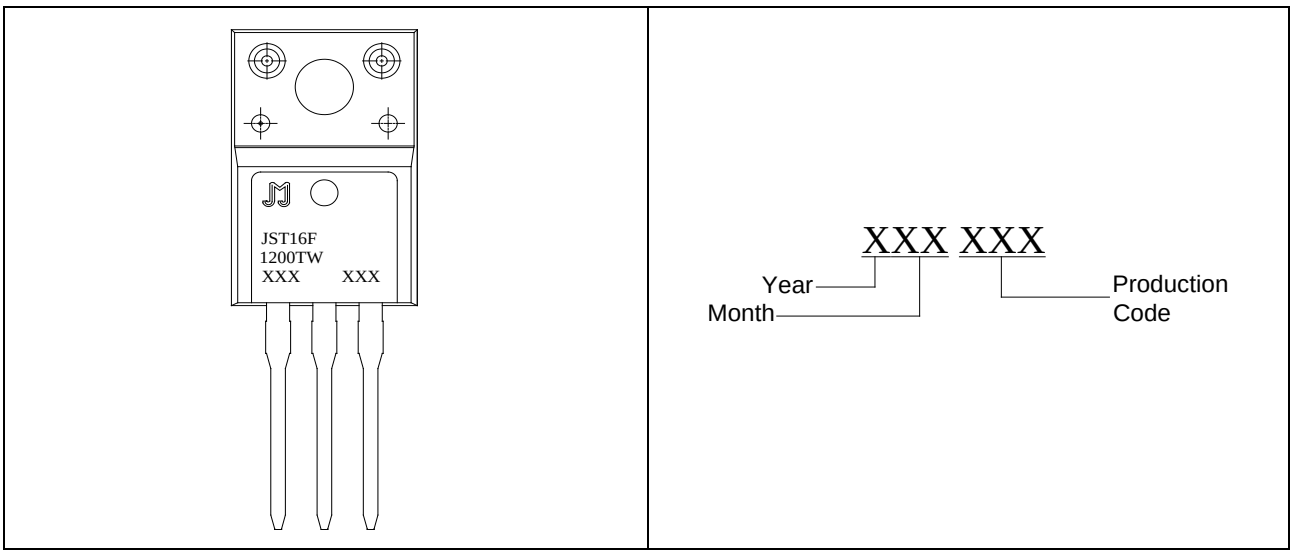
ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	5	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	15	mA
				20	
I_H	I_T =500mA		MAX.	15	mA
dV/dt	V_D=800V Gate Open T_j =125		MIN.	60	V/μs
(dI/dt)c	(dV/dt)c=10V/μs T_j=125		MIN.	1.5	A/ms
t_{on}	I_G=10mA I_A=200mA I_R=20mA T_j=25		TYP.	3	μs
t_{off}	1			25 25	1

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